International
IOR Rectifier

HF42A040SCE

Hexfred Die in Wafer Form

400 V
Size 42
5" Wafer

Electrical Characteristics (Wafer Form)

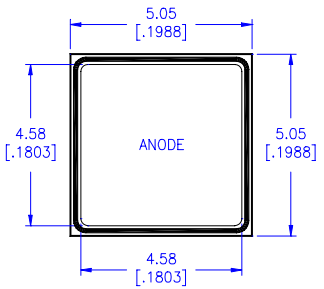
Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V_{FM}	Forward Voltage	1.2V Max.	T_J = 25°C, I_F = 60A
BV_R	Reverse Breakdown Voltage	400V Min.	T_J = 25°C, I_R = 200µA
I_{RM}	Reverse Leakage Current	6µA Max.	T_J = 25°C, V_R = 400V

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr-Ni-Ag (1kA-4kA-6kA)
Nominal Front Metal Composition, Thickness	Ti-Ni-Ag (2kA-1kA-35kA)
Chip Dimensions	0.1988" x 0.1988"
Wafer Diameter	125mm, with std. < 100 > flat
Wafer Thickness	.015" ± .003"
Relevant Die Mechanical Dwg. Number	01-5313
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Recommended Storage Environment	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : HFA120MD40C

Die Outline



NOTES:
1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)
2. CONTROLLING DIMENSION : (INCH)
3. DIMENSIONAL TOLERANCES:

BONDING PADS :	< 0.635 TOLERANCE = ± 0.013
WIDTH	< (.0250) TOLERANCE = ± (.0005)
&	> 0.635 TOLERANCE = ± 0.025
LENGTH	> (.0250) TOLERANCE = ± (.0010)
OVERALLDIE	< 1.270 TOLRANCE = ± 0.102
WIDTH	< (.050) TOLERANCE = ± (.004)
&	> 1.270 TOLERANCE = ± 0.203
LENGTH	> (.050) TOLERANCE = ± (.008)